

ABSTRACT

Provided is a semiconductor integrated circuit device, comprising: a semiconductor substrate having an SiGe layer and a first Si layer epitaxially grown thereover, and having element formation regions each partitioned by element isolation regions; a shallow groove isolation which has a groove formed in each of the element isolation regions and an insulating film inside of the groove, said groove penetrating through the first Si layer and having a bottom in the SiGe layer; a second Si layer formed between the shallow groove isolation and the SiGe layer; and a semiconductor element formed over the main surface of the semiconductor substrate in the element formation regions. The present invention enables a reduction in a leakage current via the walls of the shallow groove isolation of the strained substrate, thereby improving element isolation properties.